

Amendments to the Abstract

Please replace the original Abstract with the following amended Abstract:

An exemplary system for a four-transistor random access memory cell includes a first transistor of a first conductivity type having a gate coupled to a word line and a source coupled to a bit line, a second transistor of the first conductivity type having a gate coupled to a drain of the first transistor and a source coupled to receive a first voltage, a third transistor of a second conductivity type having a gate coupled to a drain of the second transistor, a source coupled to receive a second voltage and a drain coupled to the drain of the first transistor, and a fourth transistor of the second type having a gate coupled to the drain of the first transistor, a source coupled to receive the second voltage and a drain coupled to the drain of the second transistor.

Other systems are also provided.

Amendments to the Drawings

FIG. 3 is added the legend --Prior Art-- as suggested by Examiner. Annotated and replacement drawing sheets are attached hereto at Tab A.